

Device Modeling Report

COMPONENTS : VOLTAGE COMPARATOR
PART NUMBER : LM319N
MANUFACTURER : NATIONAL



Bee Technologies Inc.

BJT MODEL

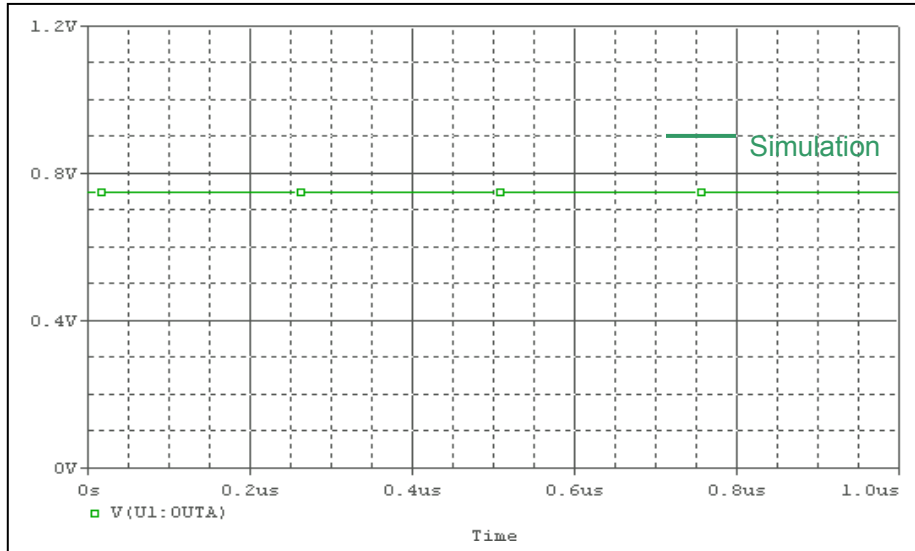
Pspice model parameter	Model description
IS	Saturation Current
BF	Ideal Maximum Forward Beta
CJC	Zero-bias Collector-Base Junction Capacitance
TF	Forward Transit Time
TR	Reverse Transit Time

DIODE MODEL

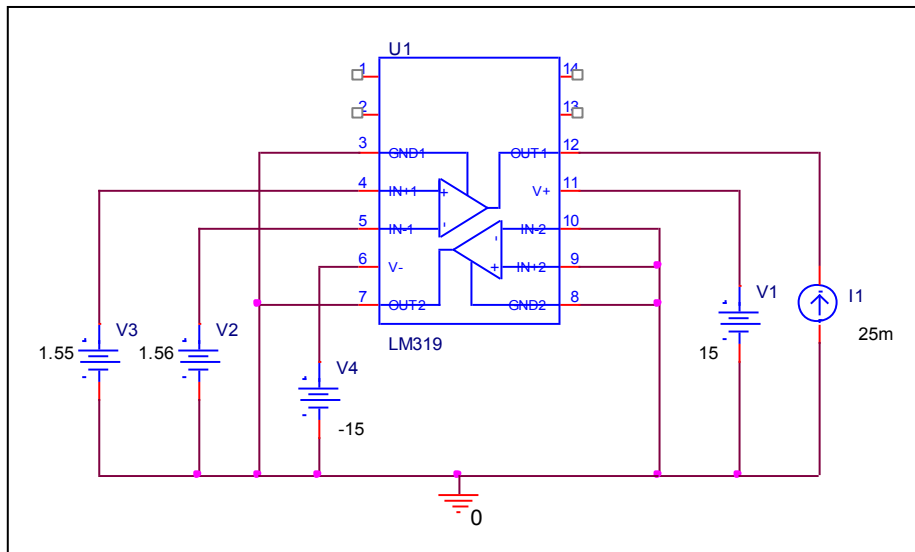
Pspice model parameter	Model description
IS	Saturation Current
RS	Series Resistance

Output Low Voltage

Simulation result



Evaluation Circuit

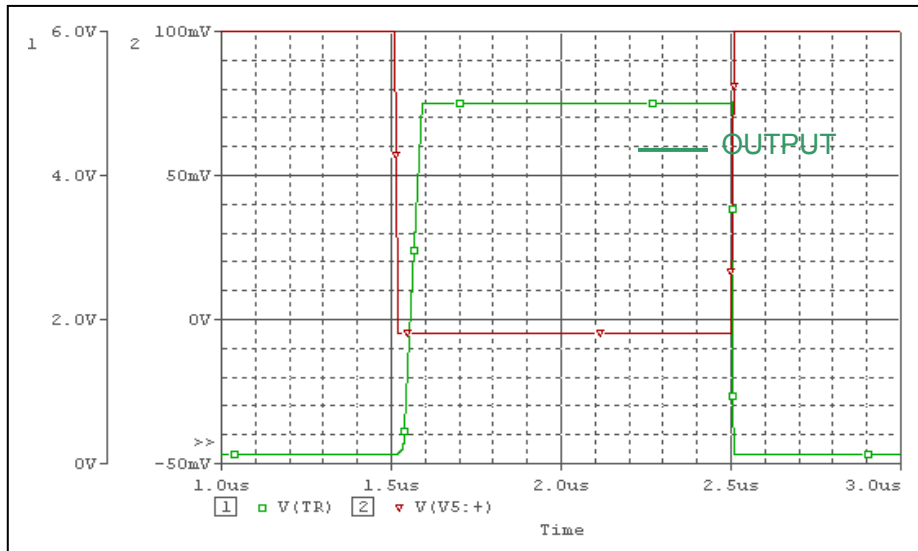


Comparison Table

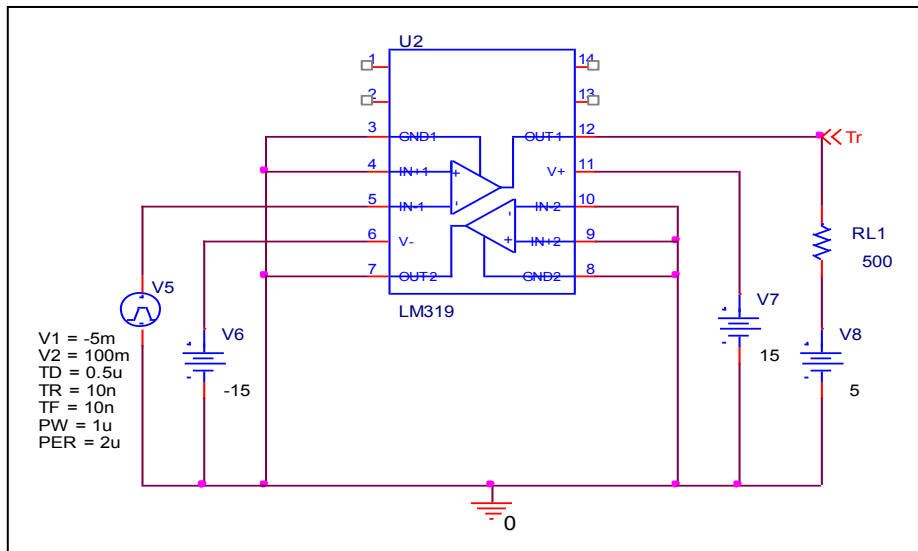
$I_o = 25\text{mA}$	Measurement	Simulation	%Error
$V_{ol} \text{ (V)}$	0.75	0.750451	0.06

Response time (Rise time and Transition time)

Simulation result



Evaluation Circuit

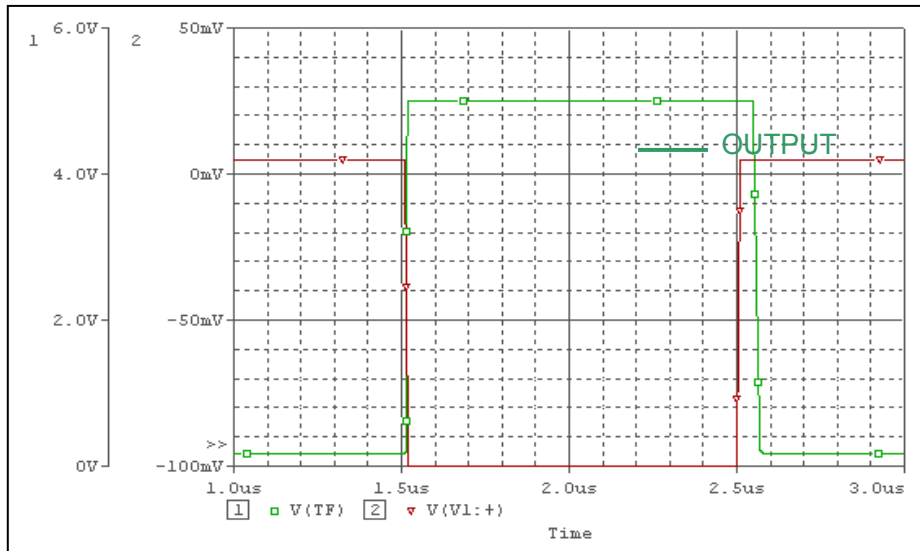


Comparison Table

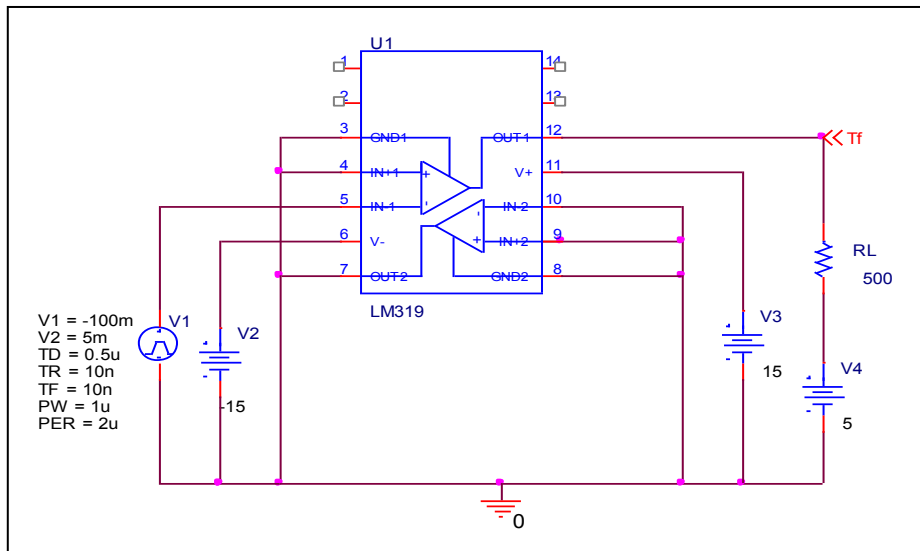
	Measurement	Simulation	% Error
Rising delay time (ns)	30	29.718	-0.940
Transition time (ns)	45	44.305	-1.544

Response time (Falling time)

Simulation result



Evaluation Circuit

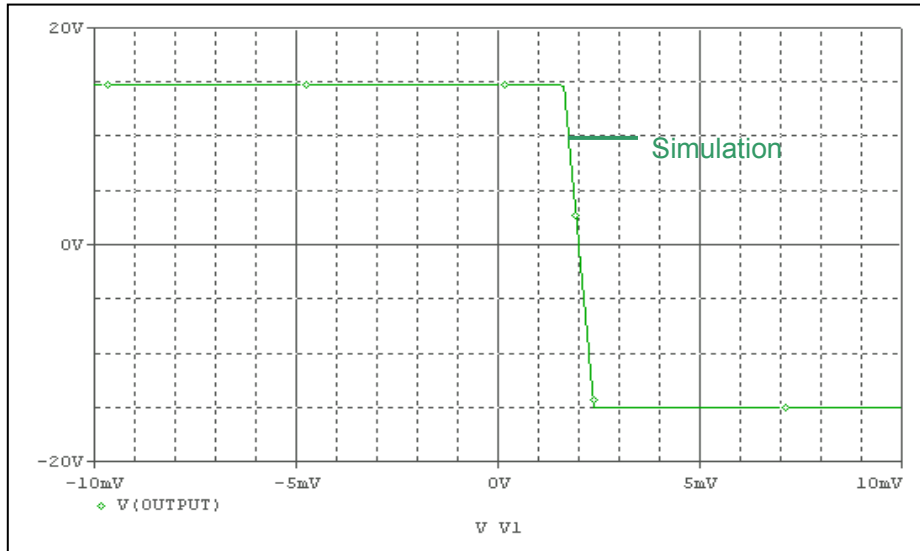


Comparison Table

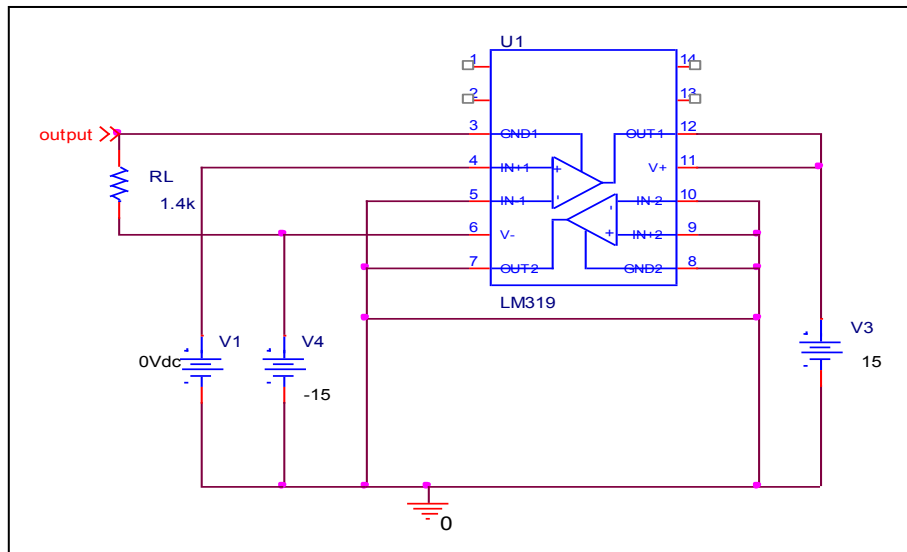
	Measurement	Simulation	% Error
Falling delay time (ns)	50	49.947	-0.106

Input Offset Voltage Characteristics

Simulation result



Evaluation Circuit

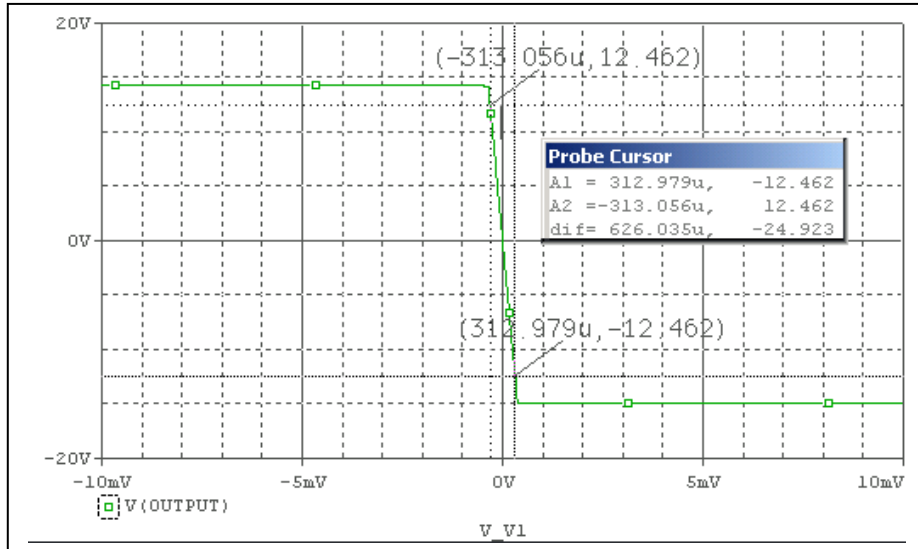


Comparison Table

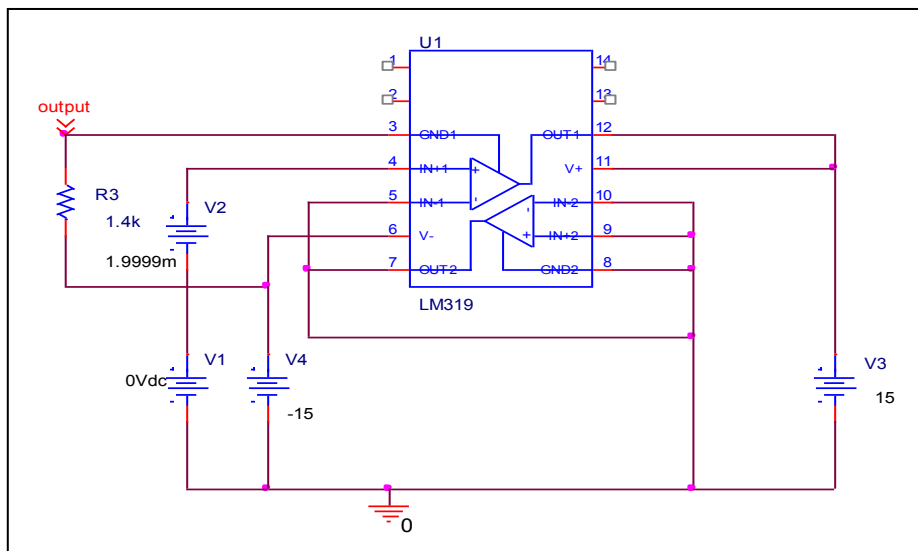
	Measurement	Simulation	%Error
$V_{io}(mV)$	2	1.9999	-0.005

Av Characteristics

Simulation result



Evaluation Circuit



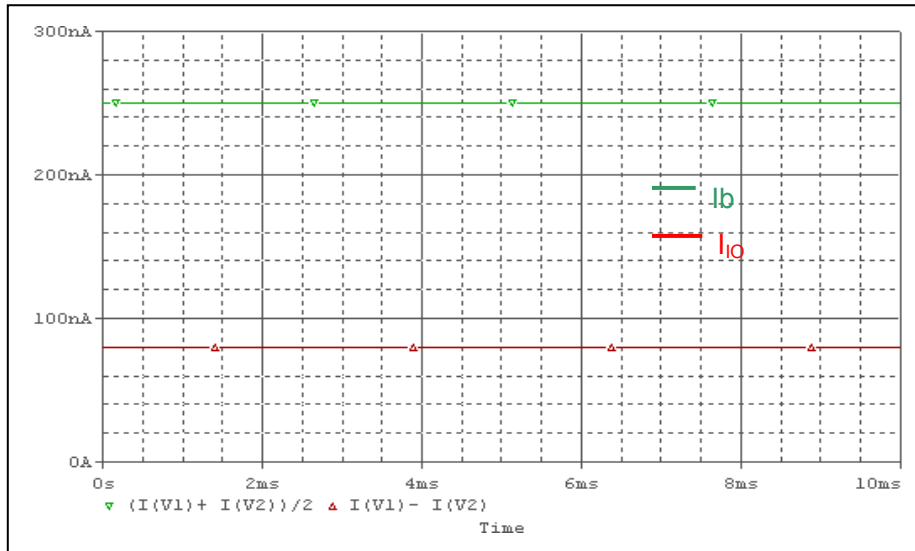
$$A_v = 24.923 / 626.035\mu$$

Comparison Table

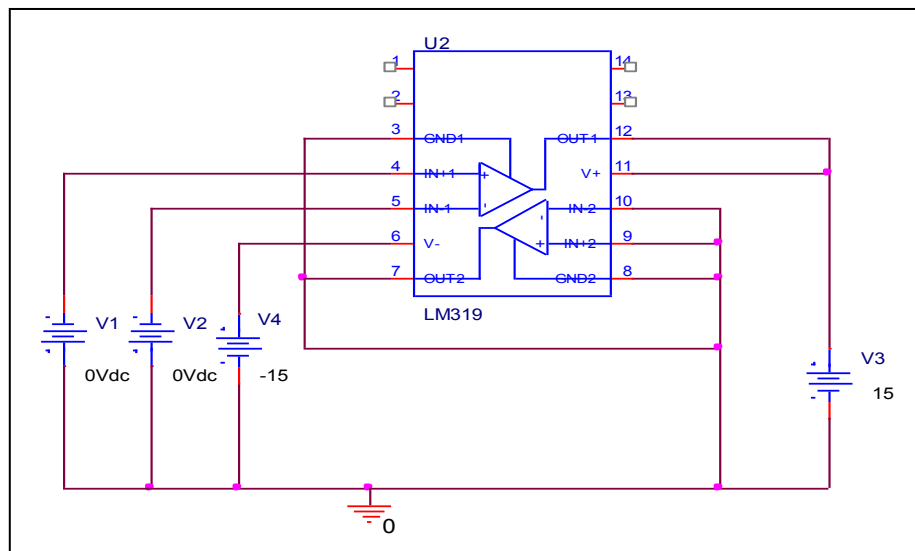
	Measurement	Simulation	%Error
Av (V/mV)	40	39.810	-0.475

Input Bias Current Characteristics

Simulation result



Evaluation Circuit



Comparison Table

	Measurement	Simulation	% Error
I_b (nA)	250	250.020	0.008
I_{io} (nA)	80	79.988	-0.015